

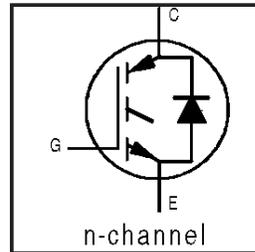
# IRG4PH30KDPbF

## INSULATED GATE BIPOLAR TRANSISTOR WITH ULTRAFAST SOFT RECOVERY DIODE

## Short Circuit Rated UltraFast IGBT

### Features

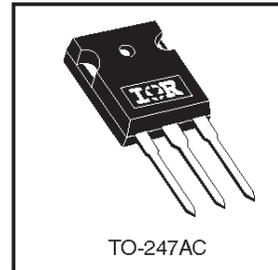
- High short circuit rating optimized for motor control,  $t_{sc} = 10\mu s$ ,  $V_{CC} = 720V$ ,  $T_J = 125^\circ C$ ,  $V_{GE} = 15V$
- Combines low conduction losses with high switching speed
- Tighter parameter distribution and higher efficiency than previous generations
- IGBT co-packaged with HEXFRED™ ultrafast, ultrasoft recovery antiparallel diodes



$V_{CES} = 1200V$
$V_{CE(on)} \text{ typ.} = 3.10V$
@ $V_{GE} = 15V, I_C = 10A$

### Benefits

- Latest generation 4 IGBT's offer highest power density motor controls possible
- HEXFRED™ diodes optimized for performance with IGBTs. Minimized recovery characteristics reduce noise, EMI and switching losses
- This part replaces IRGPH30MD2 products
- For hints see design tip 97003
- Lead-Free



### Absolute Maximum Ratings

	Parameter	Max.	Units
$V_{CES}$	Collector-to-Emitter Voltage	1200	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	20	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	10	
$I_{CM}$	Pulsed Collector Current ①	40	
$I_{LM}$	Clamped Inductive Load Current ②	40	
$I_F @ T_C = 100^\circ C$	Diode Continuous Forward Current	10	
$I_{FM}$	Diode Maximum Forward Current	40	
$t_{sc}$	Short Circuit Withstand Time	10	$\mu s$
$V_{GE}$	Gate-to-Emitter Voltage	$\pm 20$	V
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	100	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	42	
$T_J$	Operating Junction and Storage Temperature Range	-55 to +150	$^\circ C$
$T_{STG}$			
	Mounting Torque, 6-32 or M3 Screw.	10 lbf•in (1.1 N•m)	

### Thermal Resistance

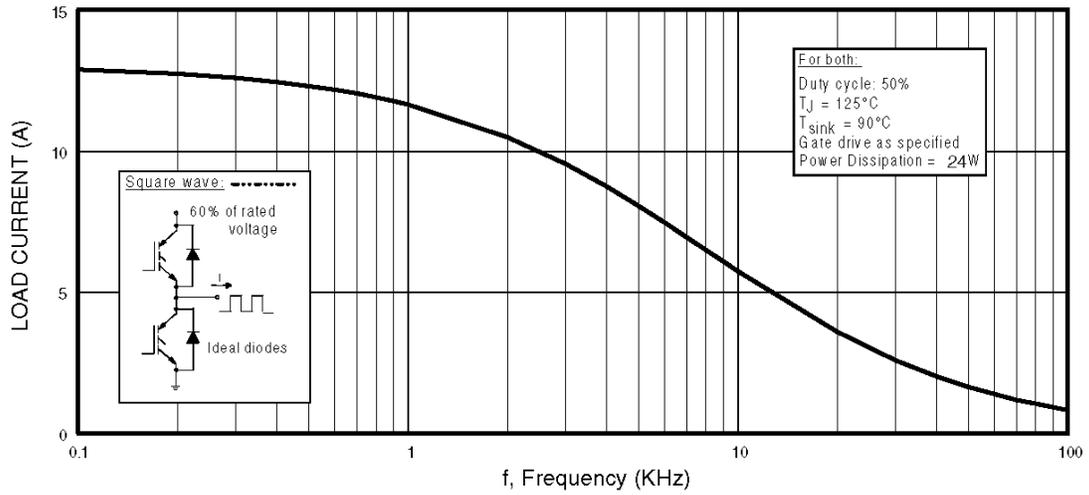
	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case - IGBT	---	---	1.2	$^\circ C/W$
$R_{\theta JC}$	Junction-to-Case - Diode	---	---	2.5	
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	---	0.24	---	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	---	---	40	
Wt	Weight	---	6 (0.21)	---	g (oz)

## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

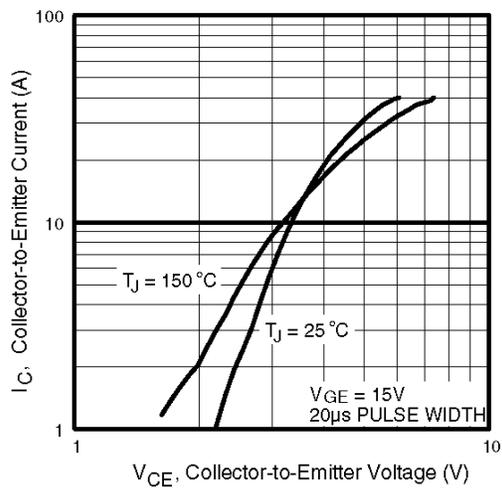
	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage <sup>③</sup>	1200	—	—	V	$V_{GE} = 0V, I_C = 250\mu A$
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.19	—	V/ $^\circ\text{C}$	$V_{GE} = 0V, I_C = 1.0mA$
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	—	3.10	4.2	V	$I_C = 10A$ $I_C = 20A$ $I_C = 10A, T_J = 150^\circ\text{C}$ $V_{GE} = 15V$ See Fig. 2, 5
		—	3.90	—		
		—	3.01	—		
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	6.0		$V_{CE} = V_{GE}, I_C = 250\mu A$
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-12	—	mV/ $^\circ\text{C}$	$V_{CE} = V_{GE}, I_C = 250\mu A$
$g_{fe}$	Forward Transconductance <sup>④</sup>	4.3	6.5	—	S	$V_{CE} = 100V, I_C = 10A$
$I_{CES}$	Zero Gate Voltage Collector Current	—	—	250	$\mu A$	$V_{GE} = 0V, V_{CE} = 1200V$ $V_{GE} = 0V, V_{CE} = 1200V, T_J = 150^\circ\text{C}$
		—	—	3500		
$V_{FM}$	Diode Forward Voltage Drop	—	3.4	3.8	V	$I_C = 10A$ $I_C = 10A, T_J = 150^\circ\text{C}$ See Fig. 13
		—	3.3	3.7		
$I_{GES}$	Gate-to-Emitter Leakage Current	—	—	$\pm 100$	nA	$V_{GE} = \pm 20V$

## Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

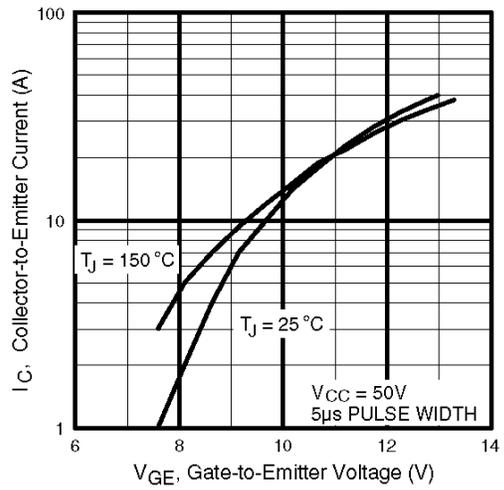
	Parameter	Min.	Typ.	Max.	Units	Conditions
$Q_g$	Total Gate Charge (turn-on)	—	53	80	nC	$I_C = 10A$ $V_{CC} = 400V$ $V_{GE} = 15V$ See Fig. 8
$Q_{ge}$	Gate - Emitter Charge (turn-on)	—	9.0	14		
$Q_{gc}$	Gate - Collector Charge (turn-on)	—	21	32		
$t_{d(on)}$	Turn-On Delay Time	—	39	—	ns	$T_J = 25^\circ\text{C}$ $I_C = 10A, V_{CC} = 800V$ $V_{GE} = 15V, R_G = 23\Omega$ Energy losses include "tail" and diode reverse recovery See Fig. 9, 10, 18
$t_r$	Rise Time	—	84	—		
$t_{d(off)}$	Turn-Off Delay Time	—	220	340		
$t_f$	Fall Time	—	90	140		
$E_{on}$	Turn-On Switching Loss	—	0.95	—		
$E_{off}$	Turn-Off Switching Loss	—	1.15	—	mJ	See Fig. 9, 10, 18
$E_{ts}$	Total Switching Loss	—	2.10	2.6		
$t_{sc}$	Short Circuit Withstand Time	10	—	—	$\mu s$	$V_{CC} = 720V, T_J = 125^\circ\text{C}$ $V_{GE} = 15V, R_G = 5.0\Omega$
$t_{d(on)}$	Turn-On Delay Time	—	42	—	ns	$T_J = 150^\circ\text{C}$ , See Fig. 10, 11, 18 $I_C = 10A, V_{CC} = 800V$ $V_{GE} = 15V, R_G = 23\Omega$ Energy losses include "tail" and diode reverse recovery
$t_r$	Rise Time	—	79	—		
$t_{d(off)}$	Turn-Off Delay Time	—	540	—		
$t_f$	Fall Time	—	97	—		
$E_{ts}$	Total Switching Loss	—	3.5	—	mJ	and diode reverse recovery
$L_E$	Internal Emitter Inductance	—	13	—	nH	Measured 5mm from package
$C_{ies}$	Input Capacitance	—	800	—	pF	$V_{GE} = 0V$ $V_{CC} = 30V$ $f = 1.0MHz$ See Fig. 7
$C_{oes}$	Output Capacitance	—	60	—		
$C_{res}$	Reverse Transfer Capacitance	—	14	—		
$t_{rr}$	Diode Reverse Recovery Time	—	50	76	ns	$T_J = 25^\circ\text{C}$ See Fig. 14 $T_J = 125^\circ\text{C}$
		—	72	110		
$I_{rr}$	Diode Peak Reverse Recovery Current	—	4.4	7.0	A	$T_J = 25^\circ\text{C}$ See Fig. 15 $T_J = 125^\circ\text{C}$
		—	5.9	8.8		
$Q_{rr}$	Diode Reverse Recovery Charge	—	130	200	nC	$T_J = 25^\circ\text{C}$ See Fig. 16 $T_J = 125^\circ\text{C}$
		—	250	380		
$di_{(rec)M}/dt$	Diode Peak Rate of Fall of Recovery During $t_b$	—	210	—	A/ $\mu s$	$T_J = 25^\circ\text{C}$ See Fig. 17 $T_J = 125^\circ\text{C}$
		—	180	—		



**Fig. 1** - Typical Load Current vs. Frequency  
 (Load Current =  $I_{\text{RMS}}$  of fundamental)

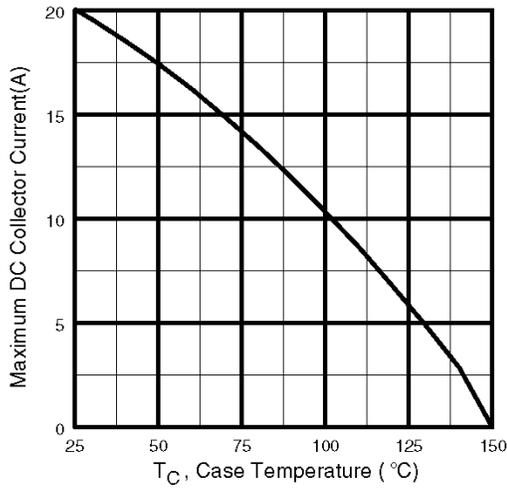


**Fig. 2** - Typical Output Characteristics

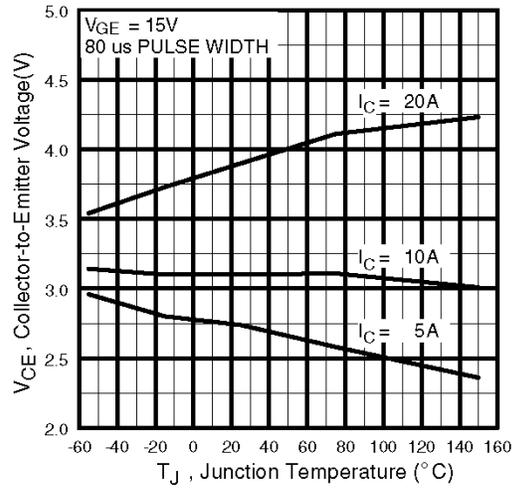


**Fig. 3** - Typical Transfer Characteristics

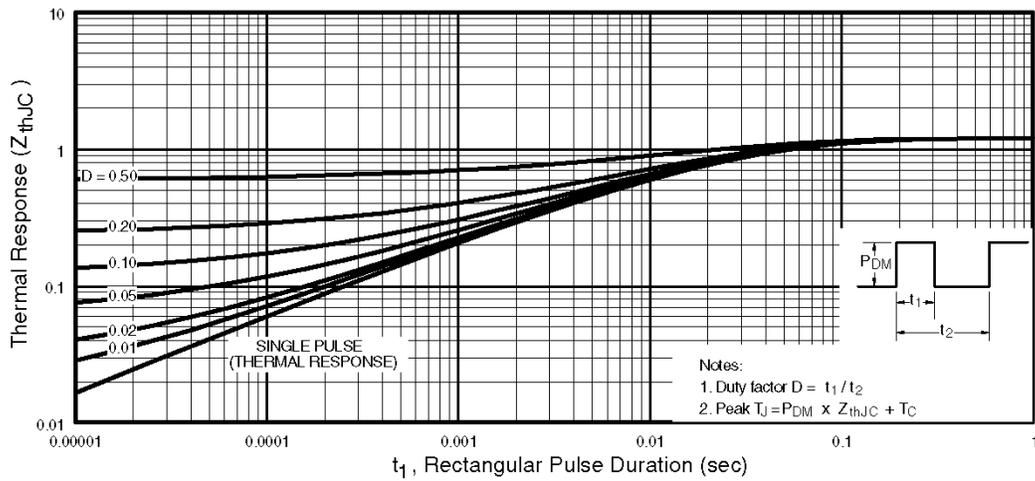
# IRG4PH30KDPbF



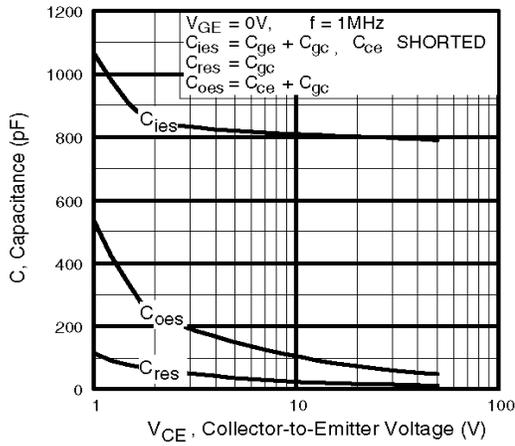
**Fig. 4** - Maximum Collector Current vs. Case Temperature



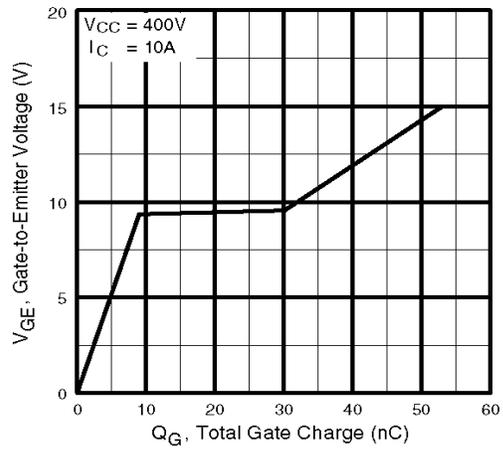
**Fig. 5** - Typical Collector-to-Emitter Voltage vs. Junction Temperature



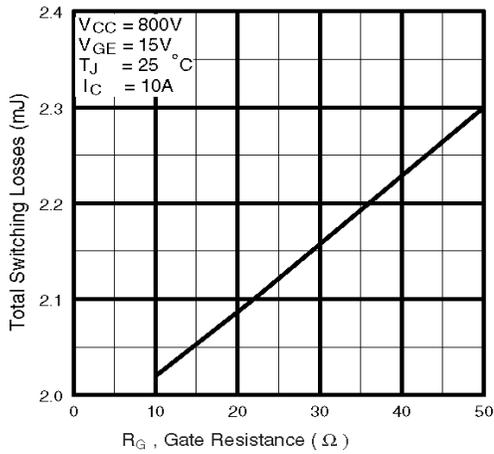
**Fig. 6** - Maximum Effective Transient Thermal Impedance, Junction-to-Case



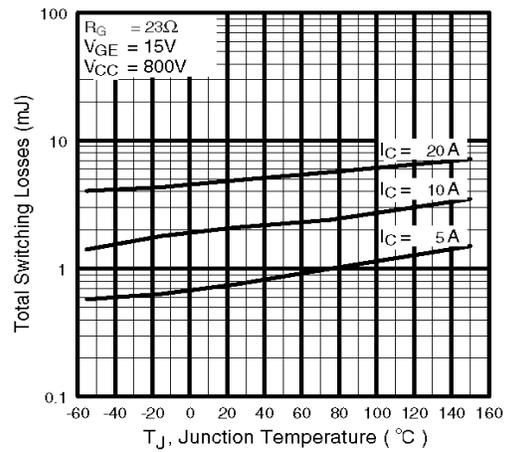
**Fig. 7** - Typical Capacitance vs. Collector-to-Emitter Voltage



**Fig. 8** - Typical Gate Charge vs. Gate-to-Emitter Voltage



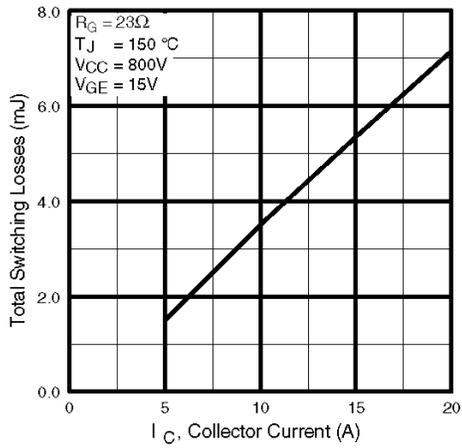
**Fig. 9** - Typical Switching Losses vs. Gate Resistance



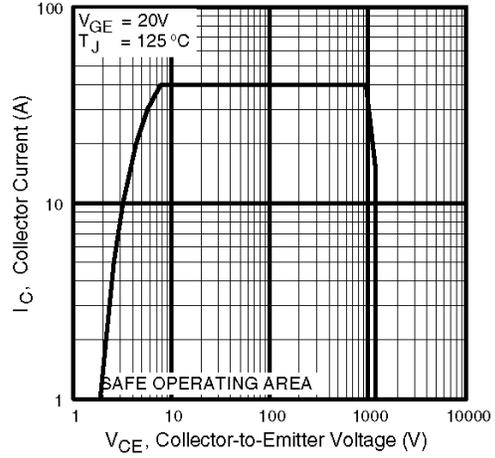
**Fig. 10** - Typical Switching Losses vs. Junction Temperature

# IRG4PH30KDPbF

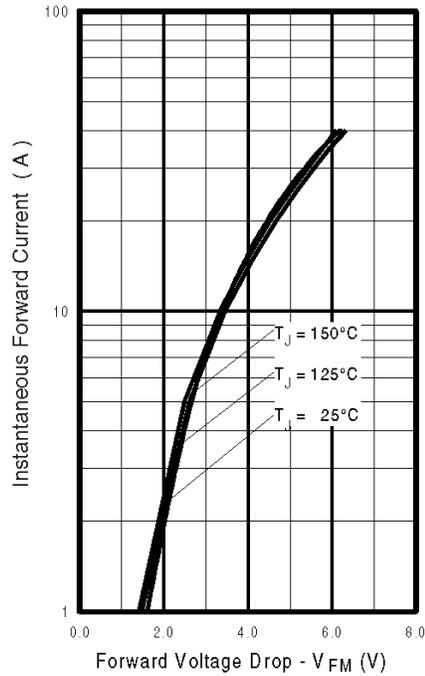
International  
**IR** Rectifier



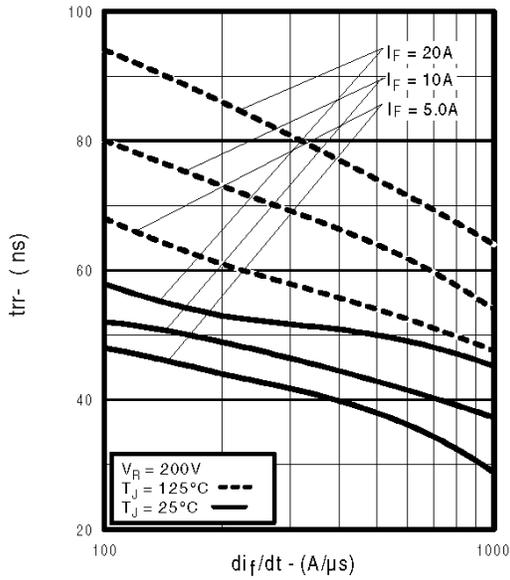
**Fig. 11** - Typical Switching Losses vs. Collector Current



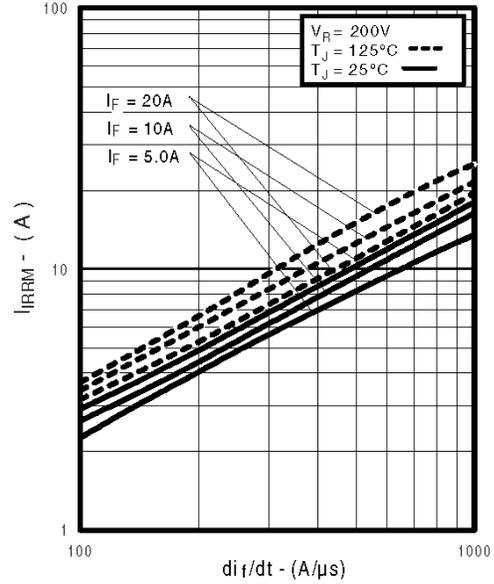
**Fig. 12** - Turn-Off SOA



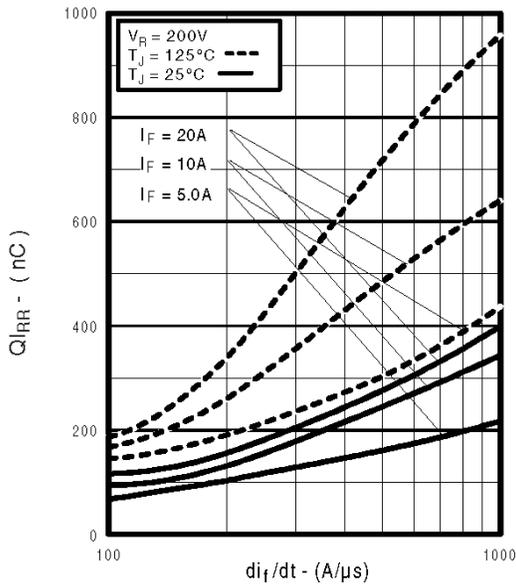
**Fig. 13** - Typical Forward Voltage Drop vs. Instantaneous Forward Current



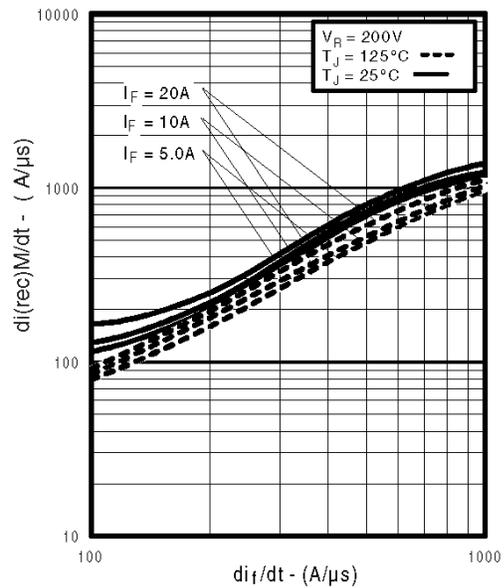
**Fig. 14** - Typical Reverse Recovery vs.  $di_f/dt$



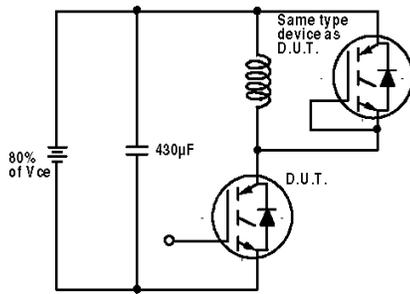
**Fig. 15** - Typical Recovery Current vs.  $di_f/dt$



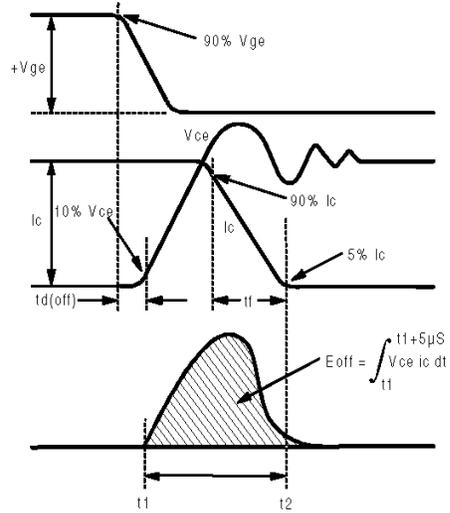
**Fig. 16** - Typical Stored Charge vs.  $di_f/dt$



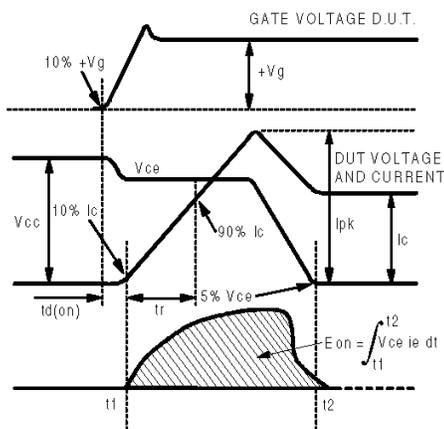
**Fig. 17** - Typical  $di_{(rec)M}/dt$  vs.  $di_f/dt$



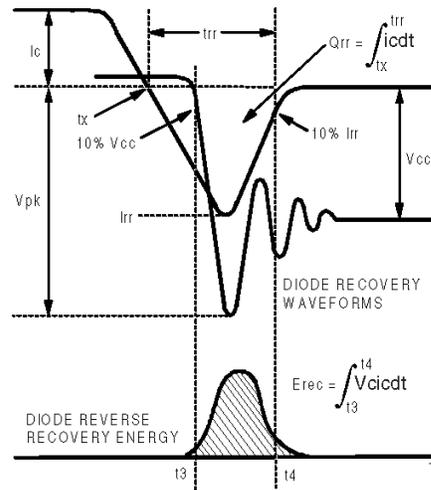
**Fig. 18a** - Test Circuit for Measurement of  $I_{LM}$ ,  $E_{on}$ ,  $E_{off}(\text{diode})$ ,  $t_{rr}$ ,  $Q_{rr}$ ,  $I_{rr}$ ,  $t_{d(on)}$ ,  $t_r$ ,  $t_{d(off)}$ ,  $t_f$



**Fig. 18b** - Test Waveforms for Circuit of Fig. 18a, Defining  $E_{off}$ ,  $t_{d(off)}$ ,  $t_f$



**Fig. 18c** - Test Waveforms for Circuit of Fig. 18a, Defining  $E_{on}$ ,  $t_{d(on)}$ ,  $t_r$



**Fig. 18d** - Test Waveforms for Circuit of Fig. 18a, Defining  $E_{rec}$ ,  $t_{tr}$ ,  $Q_{rr}$ ,  $I_{rr}$

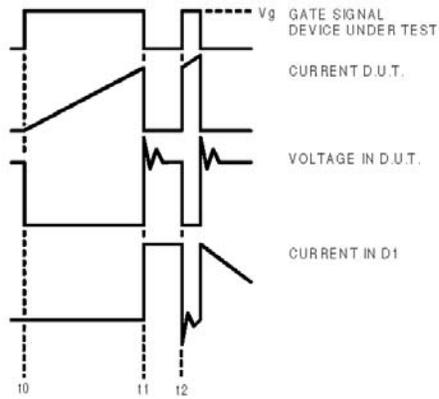


Figure 18e. Macro Waveforms for Figure 18a's Test Circuit

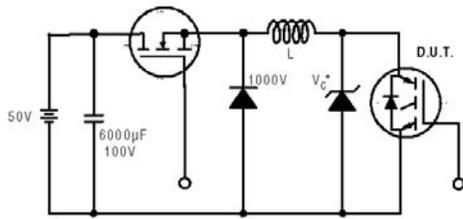


Figure 19. Clamped Inductive Load Test Circuit

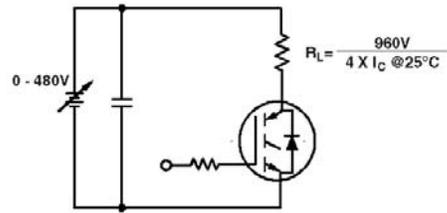


Figure 20. Pulsed Collector Current Test Circuit

# IRG4PH30KDPbF

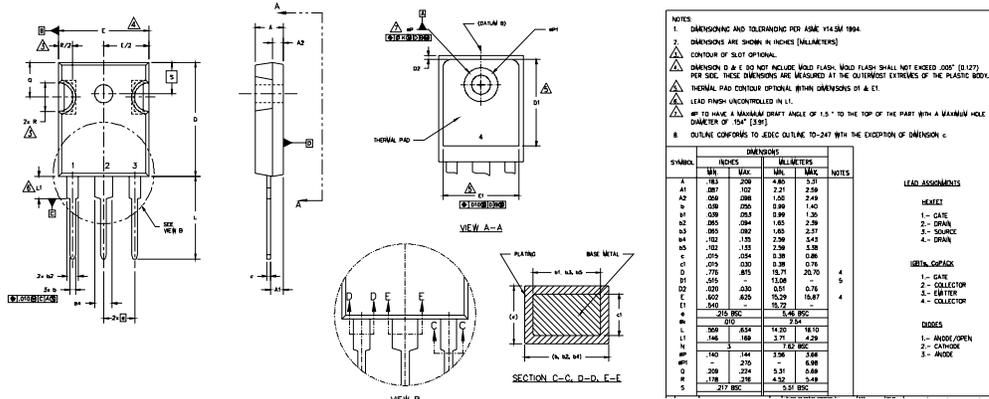
International  
Rectifier

## Notes:

- ① Repetitive rating:  $V_{GE}=20V$ ; pulse width limited by maximum junction temperature (figure 20)
- ②  $V_{CC}=80\%(V_{CES})$ ,  $V_{GE}=20V$ ,  $L=10\mu H$ ,  $R_G=23\Omega$  (figure 19)
- ③ Pulse width  $\leq 80\mu s$ ; duty factor  $\leq 0.1\%$ .
- ④ Pulse width  $5.0\mu s$ , single shot.

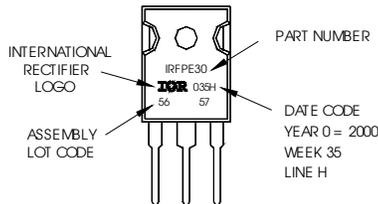
## TO-247AC Package Outline

Dimensions are shown in millimeters (inches)



## TO-247AC Part Marking Information

EXAMPLE: THIS IS AN IRFP30  
WITH ASSEMBLY  
LOT CODE 5667  
ASSEMBLED ON WW 35, 2000  
IN THE ASSEMBLY LINE "H"  
**Note:** "P" in assembly line  
position indicates "Lead-Free"



Data and specifications subject to change without notice.

International  
Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105  
TAC Fax: (310) 252-7903

Visit us at [www.irf.com](http://www.irf.com) for sales contact information.06/04

[www.irf.com](http://www.irf.com)

Note: For the most current drawings please refer to the IR website at:  
<http://www.irf.com/package/>

## Данный компонент на территории Российской Федерации

### Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

### Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: [info@moschip.ru](mailto:info@moschip.ru)

Skype отдела продаж:

moschip.ru

moschip.ru\_4

moschip.ru\_6

moschip.ru\_9